

Pradipta Dutta

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Comparison Study of DG-MOSFET with and without Gate Stack Configuration for Biosensor Applications. Silicon, 2022, 14, 3629-3640.	3.3	6
2	Improvement in the Performance of III-V Channel Based Ultra-Thin Junction-Less-Hybrid CMOS Circuits with Mixed Mode Analysis. ECS Journal of Solid State Science and Technology, 2022, 11, 051001.	1.8	1
3	Impact of Left Side Back Gate Misalignment Effect in an Analytical Tunneling Current Modeling of an Ultrathin Asymmetric DG TFET. Silicon, 2021, 13, 929-938.	3.3	0
4	Improvements in FOMs and Thermal Effects of a III-V Compound Material Based Short-Channel Thin Film Junctionless Double Gate MOSFETs. ECS Journal of Solid State Science and Technology, 2021, 10, 111006.	1.8	1
5	Improvement of transconductance and cut-off frequency in $\text{In}_{0.1}\text{Ga}_{0.9}\text{N}$ back-barrier-based double-channel $\text{Al}_{0.3}\text{Ga}_{0.7}\text{N}/\text{AlGaIn}$ high electron mobility transistor by enhancing the drain source contact length ratio. Pramana - Journal of Physics, 2020, 94, 1.	1.8	4
6	Impact of high mobility III-V compound material of a short channel thin-film SiGe double gate junctionless MOSFET as a source. Engineering Reports, 2020, 2, e12086.	1.7	11
7	Short-channel drain current model for asymmetric heavily/lightly doped DG MOSFETs. Pramana - Journal of Physics, 2017, 89, 1.	1.8	3
8	Improvement of transconductance and gate source capacitance of $\text{Al}_{0.27}\text{Ga}_{0.73}\text{N}/\text{GaIn}/\text{Ga}_{0.9}\text{N}$ back-barrier. , 2017, , .		1
9	Performance enhancement in $\text{Al}_{0.3}\text{Ga}_{0.7}\text{N}/\text{GaIn}$ HEMT based inverter using MOSHEMT. , 2017, , .		0
10	Performance analysis of junctionless double gate MOSFET using Silicon and $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$. , 2016, , .		3
11	An Analytical BTBT Current Model of Symmetric/Asymmetric 4T Tunnel Double Gate FETs With Ambipolar Characteristic. IEEE Transactions on Electron Devices, 2016, 63, 2700-2707.	3.0	6
12	A 2-D surface-potential-based threshold voltage model for short channel asymmetric heavily doped DG MOSFETs. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2014, 27, 682-690.	1.9	6
13	Muti-Carrier CDMA overview with BPSK modulation in Rayleigh channel. , 2010, , .		12
14	Controlling of Floating-Body and Thermal Conductivity in Short Channel SOI MOSFET at 30Ånm Channel Node. Silicon, 0, , 1.	3.3	1
15	A dual gate material tunnel field effect transistor model incorporating two-dimensional Poisson and Schrodinger wave equations. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 0, , e2933.	1.9	2